

## Dual P-Channel 1.8-V (G-S) MOSFET

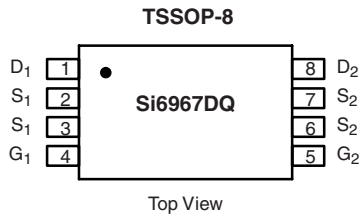
| PRODUCT SUMMARY     |                                    |                    |
|---------------------|------------------------------------|--------------------|
| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (Ω)            | I <sub>D</sub> (A) |
| - 8                 | 0.030 at V <sub>GS</sub> = - 4.5 V | ± 5.0              |
|                     | 0.045 at V <sub>GS</sub> = - 2.5 V | ± 4.0              |
|                     | 0.070 at V <sub>GS</sub> = - 1.8 V | ± 3.0              |

### FEATURES

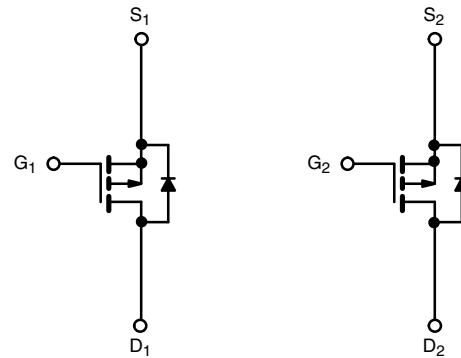
- Halogen-free
- TrenchFET® Power MOSFETs: 1.8 V Rated



**RoHS**  
COMPLIANT



Ordering Information: Si6967DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



| ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted |                                   |                        |       |   |
|---|-----------------------------------|------------------------|-------|---|
| Parameter   | Symbol                            | Limit                  | Unit  |   |
| Drain-Source Voltage  | V <sub>DS</sub>                   | - 8                    | V     |   |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ± 8                    |       |   |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>      | I <sub>D</sub>                    | T <sub>A</sub> = 25 °C | ± 5.0 | A |
|   |                                   | T <sub>A</sub> = 70 °C | ± 4.0 |   |
| Pulsed Drain Current  | I <sub>DM</sub>                   | ± 30                   |       |   |
| Continuous Source Current (Diode Conduction) <sup>a, b</sup>            | I <sub>S</sub>                    | - 1.25                 |       |   |
| Maximum Power Dissipation <sup>a, b</sup>                               | P <sub>D</sub>                    | T <sub>A</sub> = 25 °C | 1.1   | W |
|   |                                   | T <sub>A</sub> = 70 °C | 0.72  |   |
| Operating Junction and Storage Temperature Range                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150            | °C    |   |

| THERMAL RESISTANCE RATINGS               |                   |              |         |      |  |
|--|-------------------|--------------|---------|------|--|
| Parameter                                | Symbol            | Typical      | Maximum | Unit |  |
| Maximum Junction-to-Ambient <sup>a</sup> | R <sub>thJA</sub> | t ≤ 10 s     | 110     | °C/W |  |
|  |                   | Steady State | 115     |      |  |

Notes:

a. Surface Mounted on FR4 board.

b. t ≤ 10 s.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>.

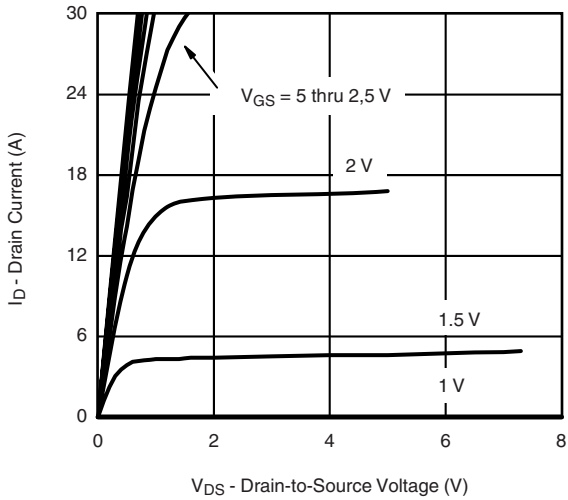
| <b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted |              |  |        |        |           |               |
|---|--------------|--|--------|--------|-----------|---------------|
| Parameter   | Symbol       | Test Conditions  | Min.   | Typ.   | Max.      | Unit          |
| <b>Static</b>   |              |  |        |        |           |               |
| Gate Threshold Voltage  | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$   | - 0.45 |        |           | V             |
| Gate-Body Leakage   | $I_{GSS}$    | $V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$   |        |        | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current   | $I_{DSS}$    | $V_{DS} = -6.4\text{ V}, V_{GS} = 0\text{ V}$  |        |        | - 1       | $\mu\text{A}$ |
|   |              | $V_{DS} = -6.4\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$  |        |        | - 25      |               |
| On-State Drain Current <sup>a</sup>   | $I_{D(on)}$  | $V_{DS} \geq -8\text{ V}, V_{GS} = -4.5\text{ V}$  | - 30   |        |           | A             |
| Drain-Source On-State Resistance <sup>a</sup>                                   | $R_{DS(on)}$ | $V_{GS} = -4.5\text{ V}, I_D = -5.0\text{ A}$  |        | 0.024  | 0.030     | $\Omega$      |
|   |              | $V_{GS} = -2.5\text{ V}, I_D = -4.0\text{ A}$  |        | 0.033  | 0.045     |               |
|   |              | $V_{GS} = -1.8\text{ V}, I_D = -3.0\text{ A}$  |        | 0.048  | 0.070     |               |
| Forward Transconductance <sup>a</sup>   | $g_{fs}$     | $V_{DS} = -8\text{ V}, I_D = -5.0\text{ A}$  |        | 18     |           | S             |
| Diode Forward Voltage <sup>a</sup>  | $V_{SD}$     | $I_S = -1.25\text{ A}, V_{GS} = 0\text{ V}$  |        | - 0.68 | - 1.1     | V             |
| <b>Dynamic<sup>b</sup></b>  |              |  |        |        |           |               |
| Total Gate Charge   | $Q_g$        | $V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5.0\text{ A}$  |        | 20     | 40        | nC            |
| Gate-Source Charge  | $Q_{gs}$     |  | 4.5    |        |           |               |
| Gate-Drain Charge   | $Q_{gd}$     |  | 3.6    |        |           |               |
| Turn-On Delay Time  | $t_{d(on)}$  | $V_{DD} = -6\text{ V}, R_L = 6\text{ }\Omega$<br>$I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$ |        | 20     | 50        | ns            |
| Rise Time   | $t_r$        |  |        | 30     | 60        |               |
| Turn-Off Delay Time   | $t_{d(off)}$ |  |        | 85     | 150       |               |
| Fall Time   | $t_f$        |  |        | 50     | 90        |               |
| Source-Drain Reverse Recovery Time  | $t_{rr}$     | $I_F = -1.25\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$   |        | 50     | 100       |               |

## Notes:

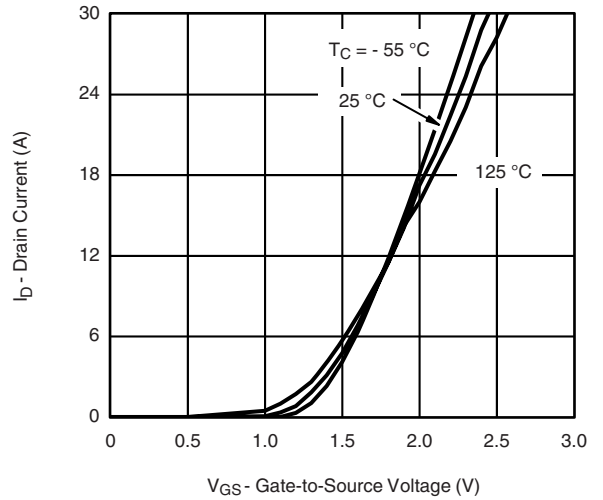
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

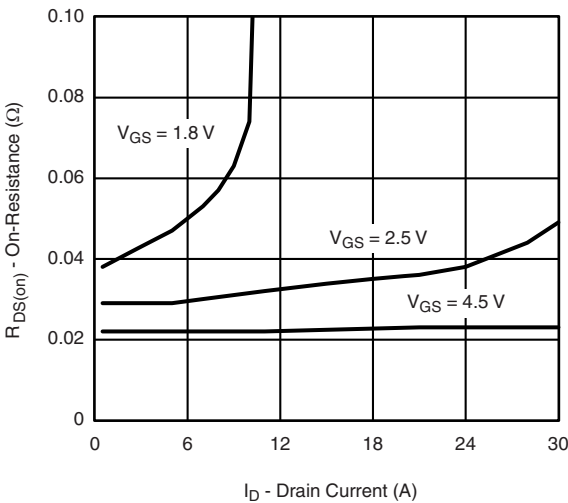
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



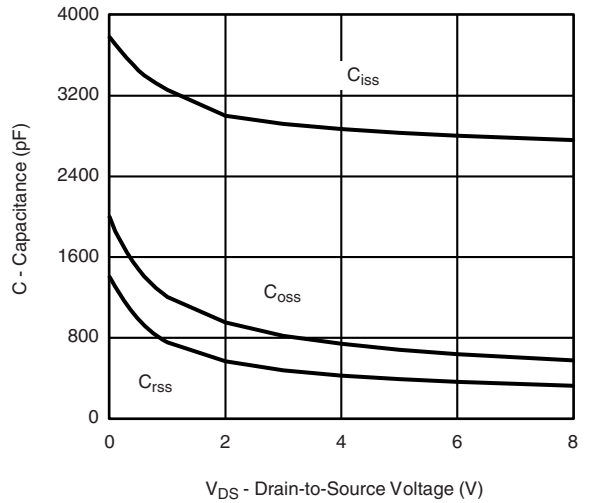
**Output Characteristics**



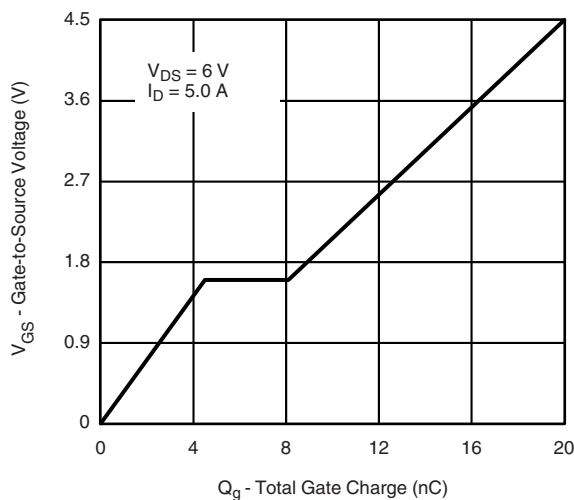
**Transfer Characteristics**



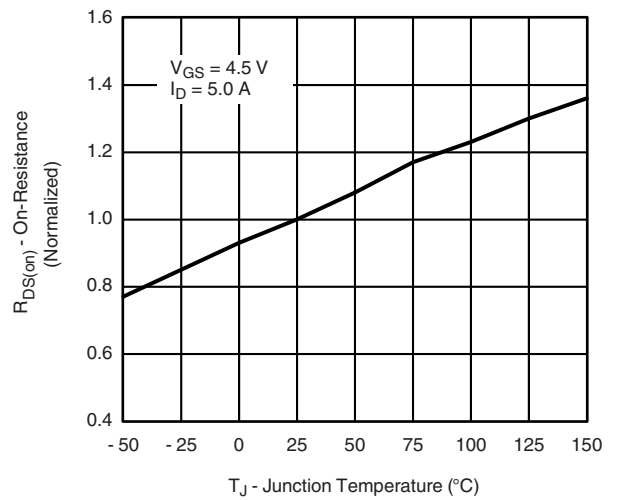
**On-Resistance vs. Drain Current**



**Capacitance**

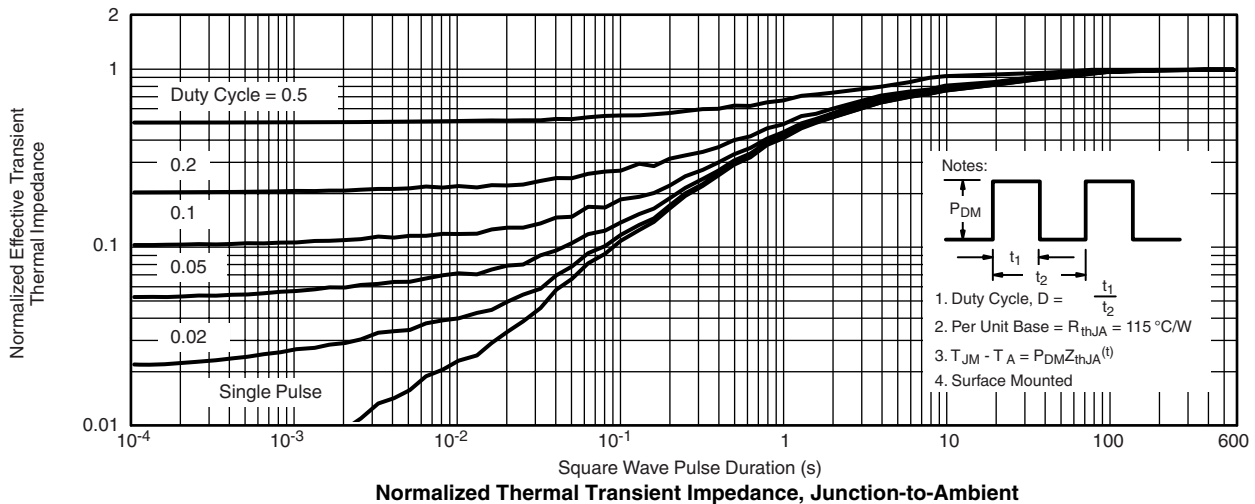
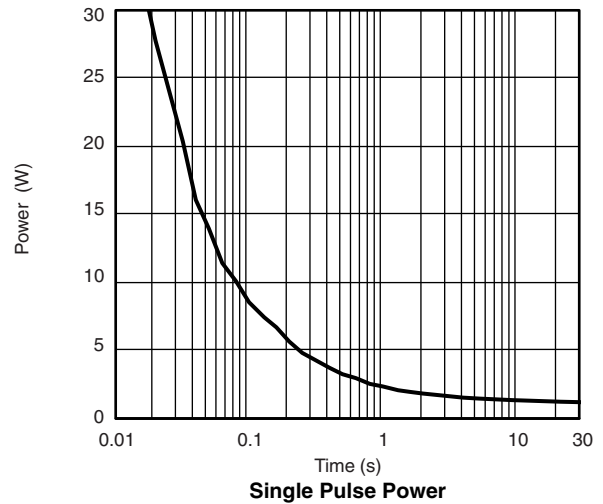
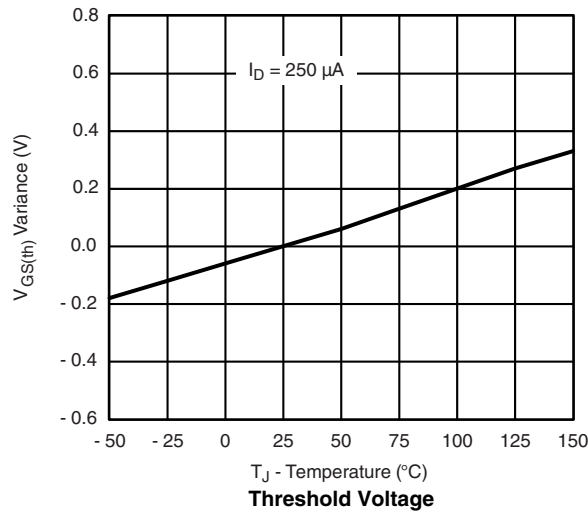
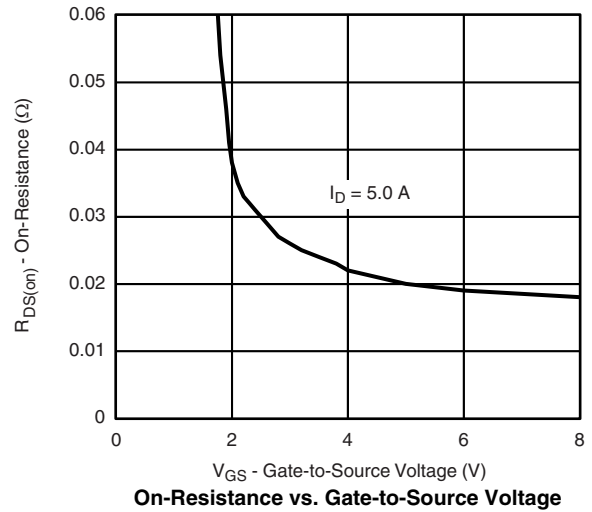
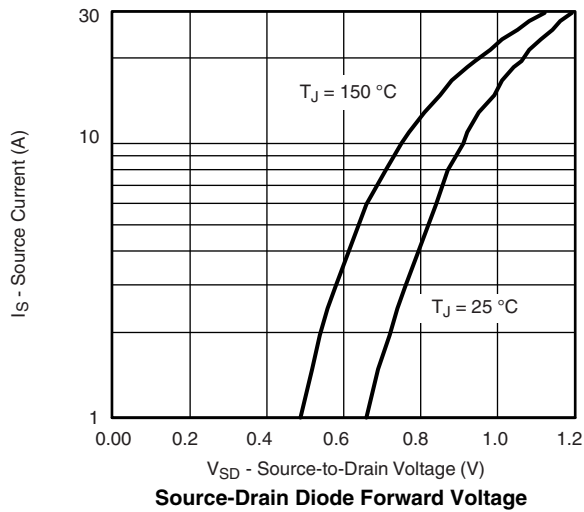


**Gate Charge**



**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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